

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

SMP3003 — General-Purpose Switching Device Applications

Features

- ON-resistance RDS(on)1=6.2m Ω (typ.)
- Input capacitance Ciss=13400pF
- · 4V drive

Specifications

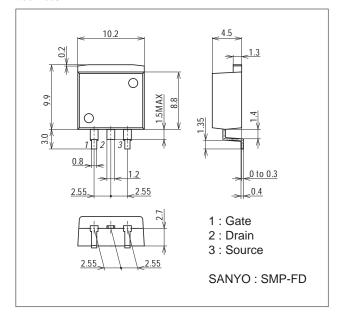
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-75	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		-100	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-400	А
Allowable Power Dissipation	PD	Tc=25°C	90	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	EAS		468	mJ
Avalanche Current *2	I _{AV}		-60	А

Note: *1 V_{DD}=-48V, L=100μH, I_AV=-60A (Fig.1)

Package Dimensions

unit : mm (typ) 7001-003



Product & Package Information

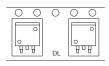
• Package : SMP-FD

• JEITA, JEDEC : SC-83, TO-220SMD

SOT-404, D2PAK

• Minimum Packing Quantity: 1000 pcs./reel

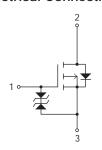
Packing Type: DL



Marking



Electrical Connection



^{*2} L≤100µH, Single pulse

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-75			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-75V, V _{GS} =0V			-10	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	V _{GS} (off)	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	yfs	V _D S=-10V, I _D =-50A		140		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =-50A, V _G S=-10V		6.2	8.0	mΩ
	R _{DS} (on)2	I _D =-50A, V _G S=-4V		8.0	11	mΩ
Input Capacitance	Ciss	V _{DS} =-20V, f=1MHz		13400		pF
Output Capacitance	Coss			1000		pF
Reverse Transfer Capacitance	Crss			740		pF
Turn-ON Delay Time	t _d (on)			95		ns
Rise Time	t _r	Con Fig 2		1000		ns
Turn-OFF Delay Time	t _d (off)	See Fig.2		800		ns
Fall Time	tf			820		ns
Total Gate Charge	Qg	V _{DS} =-48V, V _{GS} =-10V, I _D =-100A		280		nC
Gate-to-Source Charge	Qgs			50		nC
Gate-to-Drain "Miller" Charge	Qgd			55		nC
Diode Forward Voltage	VSD	IS=-100A, VGS=0V		-1.0	-1.5	V
Reverse Recovery Time	t _{rr}	See Fig.3		120		ns
Reverse Recovery Charge	Q _{rr}	IS=-100A, VGS=0V, di/dt=-100A/μs		380		nC

Fig.1 Avalanche Resistance Test Circuit

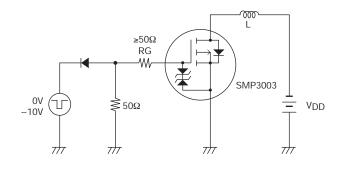


Fig.2 Switching Time Test Circuit

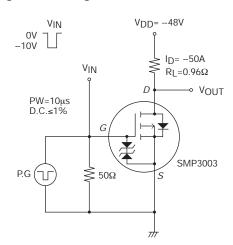
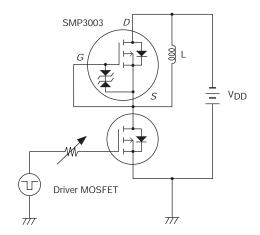
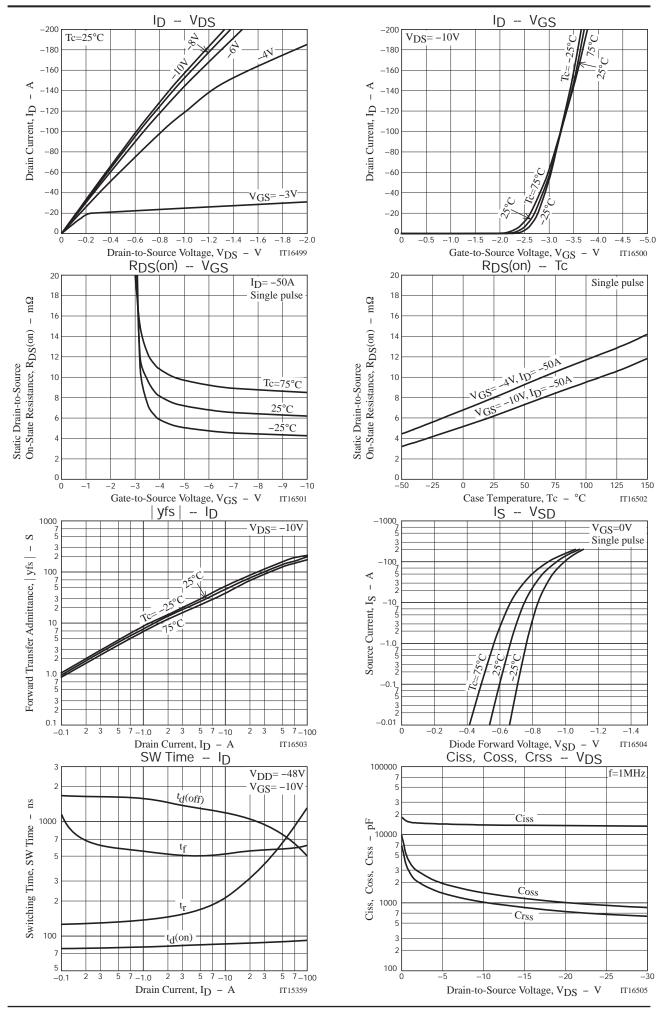
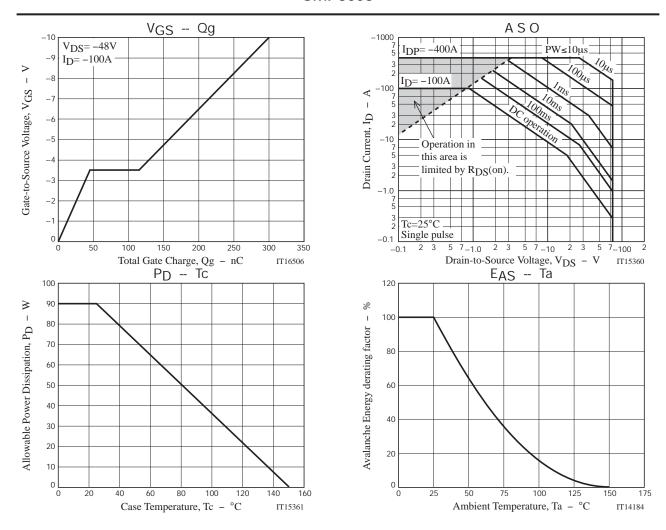


Fig.3 Reverse Recovery Time Test Circuit







Note on usage: Since the SMP3003 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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